Seat No.: Enrolment No.

GUJARAT TECHNOLOGICAL UNIVERSITY M. E. - SEMESTER - III • EXAMINATION - WINTER • 2013

Su	bject	code: 734202 Date: 28-11-2013	
Ti	me: 1	Name: IC Fabrication Technology 0:30 am – 13:00 pm Total Marks: 70 tions: Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks.	
Q.1	(a) (b)	List down the steps for preparation of wafer and explain each in brief. Explain the different crystalline orientation for wafer in detail.	07 07
Q.2	(a) (b)	Explain the different types of wafer based on wafer cut. What is clean room why it is needed? OR	07 07
	(b)	What is Etching? Explain plasma etching.	07
Q.3	(a) (b)	List down the steps for preparation of IC and explain each in brief. Explain need of shallow junction in smaller geometry devices for VLSI Design? OR	07 07
Q.3	(a) (b)	Give the classifications of clean room. Which resist is used in Electron-Beam Lithography? Explain Electron-Beam Lithography.	07 07
Q.4	(a)	Explain RF magnetron sputtering to deposit Al alloys for shallow junction device.	07
	(b)	Give comparison between Positive and Negative resist. OR	07
Q.4	(a) (b)	What is metallization? Explain PVD. Explain role of O ₂ in furnace diffusion process. Explain Solid Solubility.	07 07
Q.5	(a) (b)	Explain the types of contamination present in clean room. What is oxidation? Why it is needed?	07 07
Q.5	(a)	OR Explain different Oxidation Induced Effects	07

(b)

for mask layers.

Why alignment is necessary in photolithography. Describe alignment techniques

07